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Spin-Filter induced Large Magnetoresistance in 2D van der Waals Magnetic junctions

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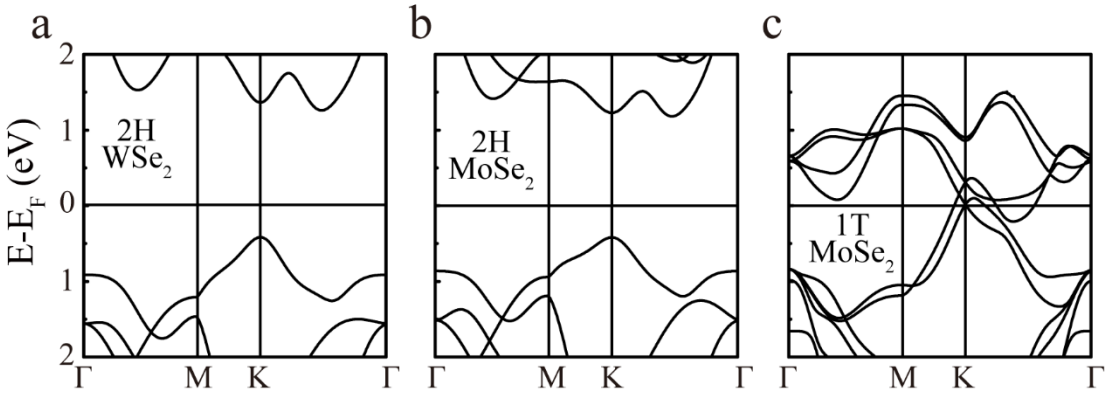

Figure S1 The band structure of 2H WSe_2, 2H $MoSe_2$ and 1T $MoSe_2$.

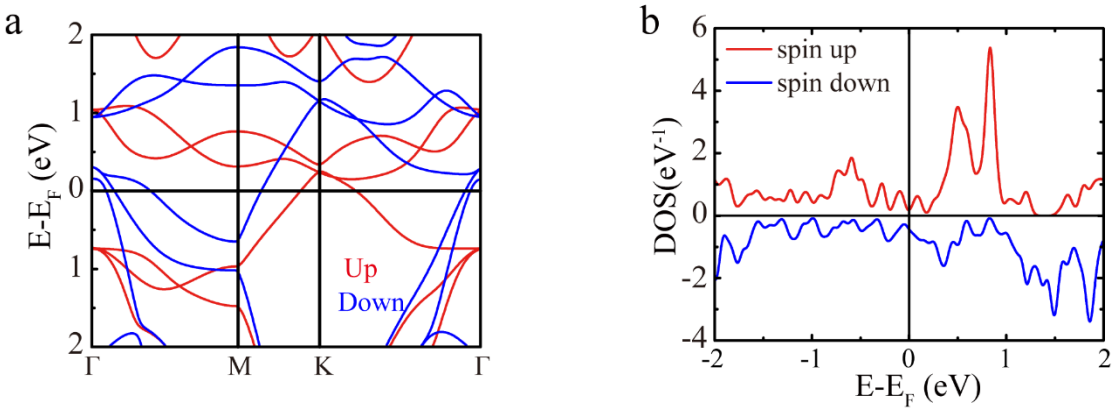

Figure S2 The electronic property of 1T VSe_2. a) The band structure of VSe_2. b) The spin-resolved density of state (DOS) of VSe_2.

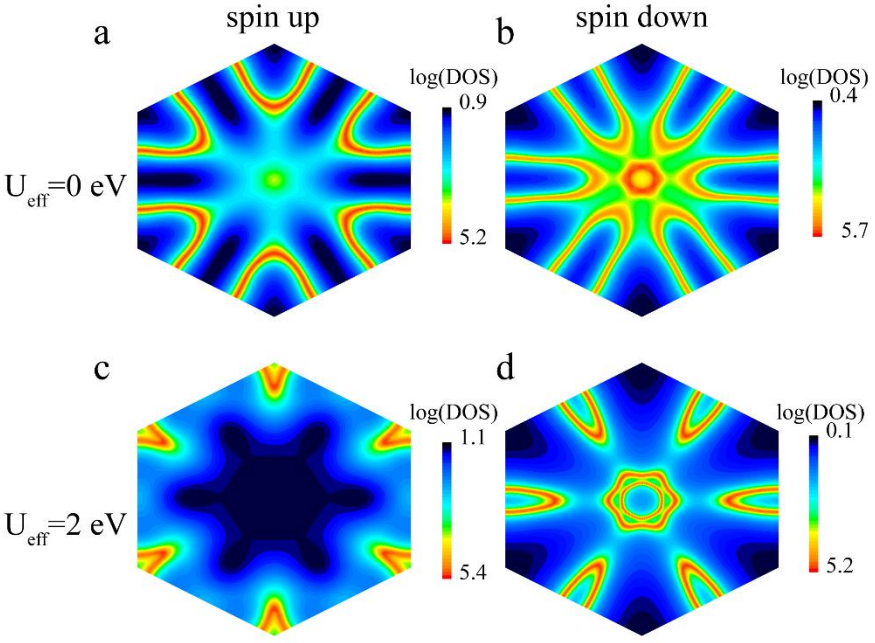

Figure S3 The influence of Hubbard term on electronic property of 1T-VSe_2. a & b) The spin up (a) and spin down (b) states with U_{eff}=0 eV. c & d) The spin up (c) and spin down (d) states with U_{eff}=2 eV.